

Memory FRAM

512K (64 K × 8) Bit SPI

MB85RS512T

■ DESCRIPTION

MB85RS512T is a FRAM (Ferroelectric Random Access Memory) chip in a configuration of 65,536 words × 8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

MB85RS512T adopts the Serial Peripheral Interface (SPI).

The MB85RS512T is able to retain data without using a back-up battery, as is needed for SRAM.

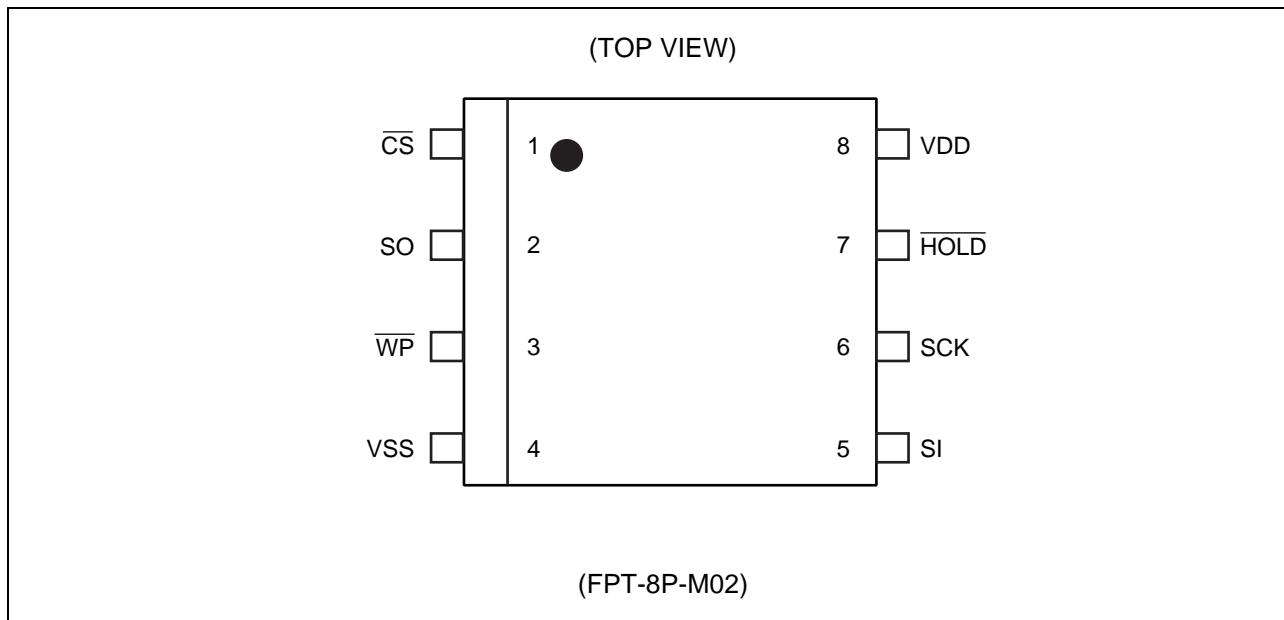
The memory cells used in the MB85RS512T can be used for 10^{13} read/write operations, which is a significant improvement over the number of read and write operations supported by Flash memory and E²PROM.

MB85RS512T does not take long time to write data like Flash memories or E²PROM, and MB85RS512T takes no wait time.

■ FEATURES

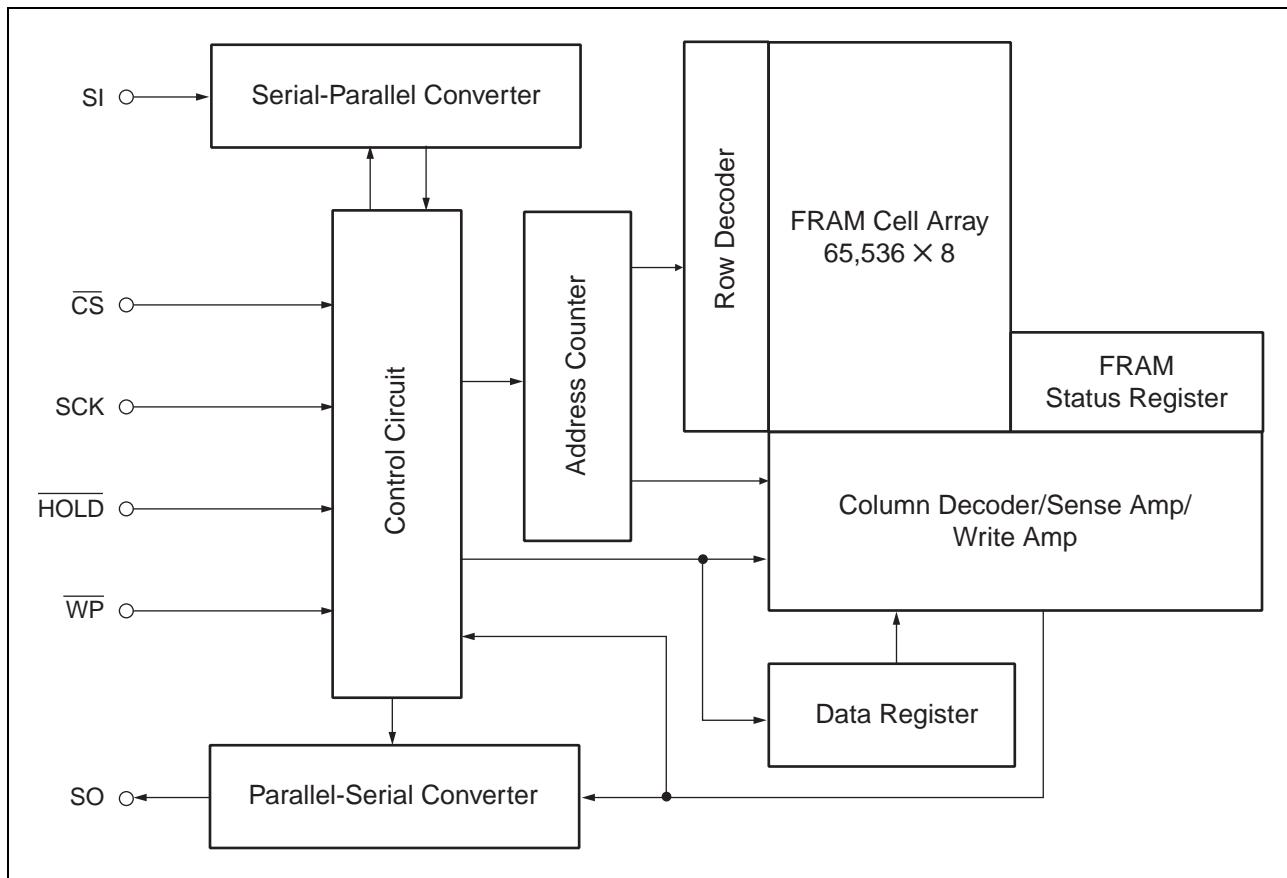
- | | |
|---------------------------------------|--|
| • Bit configuration | : 65,536 words × 8 bits |
| • Serial Peripheral Interface | : SPI (Serial Peripheral Interface)
Correspondent to SPI mode 0 (0, 0) and mode 3 (1, 1) |
| • Operating frequency | : 1.8 V to 2.7 V, 25 MHz (Max)
2.7 V to 3.6 V, 30 MHz (Max)
For FSTRD command 2.7 V to 3.6 V, 40 MHz (Max) |
| • High endurance | : 10^{13} times / byte |
| • Data retention | : 10 years (+85 °C) |
| • Operating power supply voltage | : 1.8 V to 3.6 V |
| • Low power consumption | : Operating power supply current 10 mA (Max@30 MHz)
Standby current 120 µA (Max)
Sleep current 10 µA (Max) |
| • Operation ambient temperature range | : -40 °C to +85 °C |
| • Package | : 8-pin plastic SOP (FPT-8P-M02)
RoHS compliant |

■ PIN ASSIGNMENT



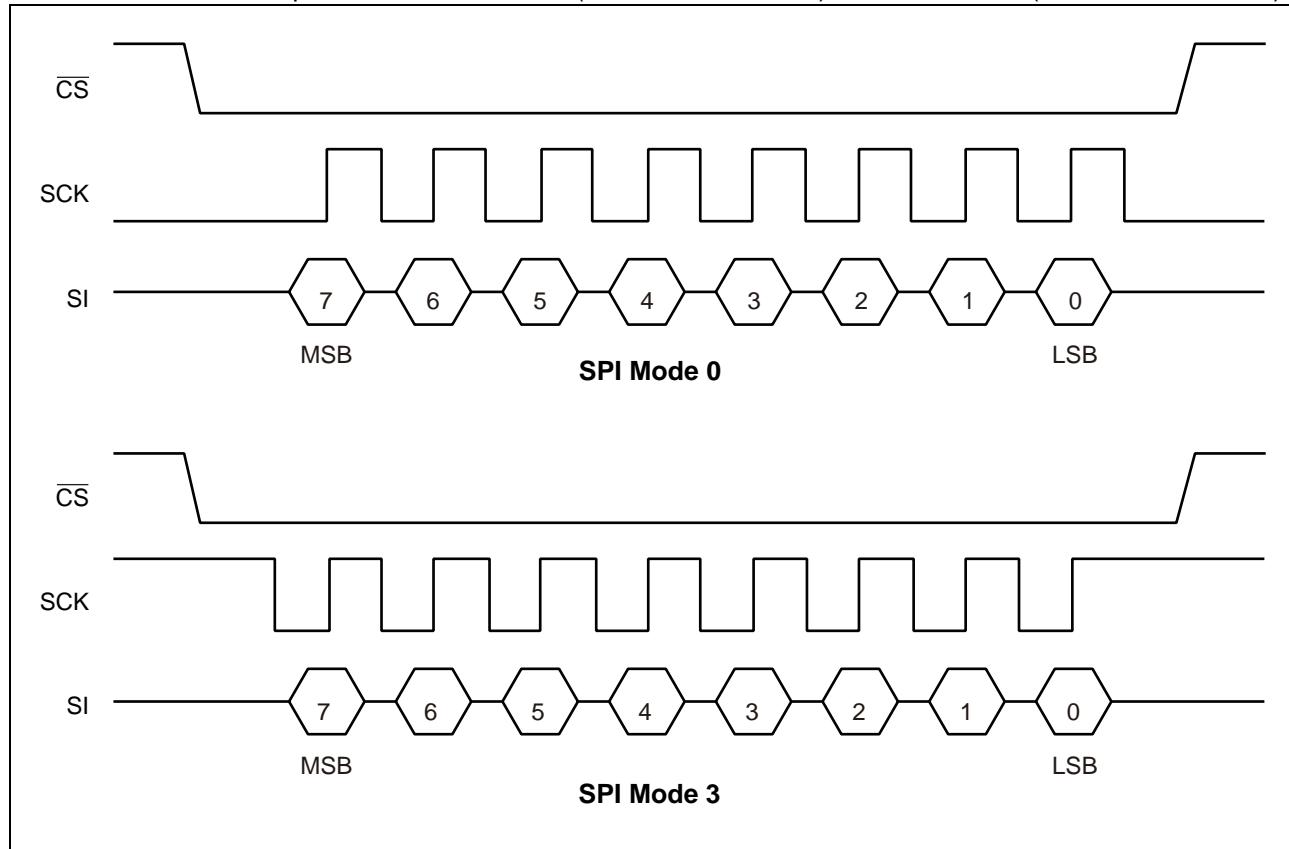
■ PIN FUNCTIONAL DESCRIPTIONS

Pin No.	Pin Name	Functional description
1	\overline{CS}	Chip Select pin This is an input pin to make chips select. When \overline{CS} is "H" level, device is in deselect (standby) status and SO becomes High-Z. Inputs from other pins are ignored for this time. When \overline{CS} is "L" level, device is in select (active) status. \overline{CS} has to be "L" level before inputting op-code. The Chip Select pin is pulled up internally to the VDD pin.
3	\overline{WP}	Write Protect pin This is a pin to control writing to a status register. The writing of status register (see "■ STATUS REGISTER") is protected in related with \overline{WP} and WPEN. See "■ WRITING PROTECT" for detail.
7	\overline{HOLD}	Hold pin This pin is used to interrupt serial input/output without making chips deselect. When \overline{HOLD} is "L" level, hold operation is activated, SO becomes High-Z, SCK and SI become do not care. While the hold operation, CS has to be retained "L" level.
6	SCK	Serial Clock pin This is a clock input pin to input/output serial data. SI is loaded synchronously to a rising edge, SO is output synchronously to a falling edge.
5	SI	Serial Data Input pin This is an input pin of serial data. This inputs op-code, address, and writing data.
2	SO	Serial Data Output pin This is an output pin of serial data. Reading data of FRAM memory cell array and status register data are output. This is High-Z during standby.
8	VDD	Supply Voltage pin
4	VSS	Ground pin

■ BLOCK DIAGRAM

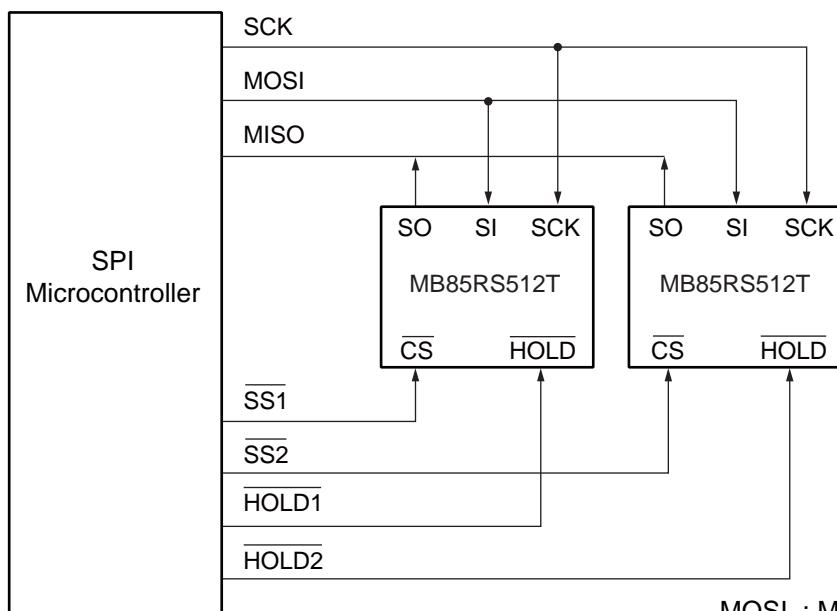
■ SPI MODE

MB85RS512T corresponds to the SPI mode 0 ($\text{CPOL}=0$, $\text{CPHA}=0$) , and SPI mode 3 ($\text{CPOL}=1$, $\text{CPHA}=1$).



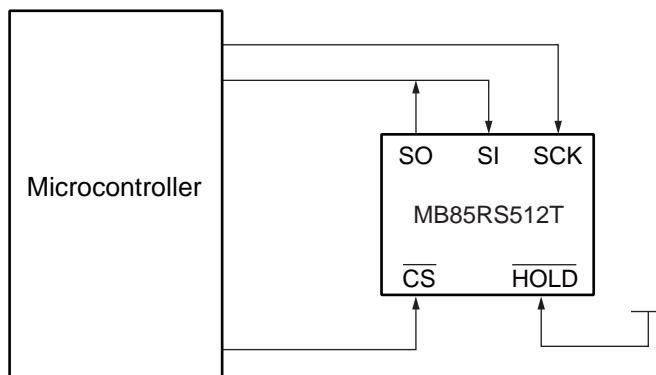
■ SERIAL PERIPHERAL INTERFACE (SPI)

MB85RS512T works as a slave of SPI. More than 2 devices can be connected by using microcontroller equipped with SPI port. By using a microcontroller not equipped with SPI port, SI and SO can be bus connected to use.



MOSI : Master Out Slave In
MISO : Master In Slave Out
SS : Slave Select

System Configuration with SPI Port



System Configuration without SPI Port

■ STATUS REGISTER

Bit No.	Bit Name	Function
7	WPEN	Status Register Write Protect This is a bit composed of nonvolatile memories (FRAM). WPEN protects writing to a status register (refer to "■ WRITING PROTECT") relating with WP input. Writing with the WRSR command and reading with the RDSR command are possible.
6 to 4	—	Not Used Bits These are bits composed of nonvolatile memories, writing with the WRSR command is possible. These bits are not used but they are read with the RDSR command.
3	BP1	Block Protect
2	BP0	This is a bit composed of nonvolatile memory. This defines size of write protect block for the WRITE command (refer to "■ BLOCK PROTECT"). Writing with the WRSR command and reading with the RDSR command are possible.
1	WEL	Write Enable Latch This indicates FRAM Array and status register are writable. The WREN command is for setting, and the WRDI command is for resetting. With the RDSR command, reading is possible but writing is not possible with the WRSR command. WEL is reset after the following operations. After power ON. After WRDI command recognition. The rising edge of CS after WRSR command recognition. The rising edge of CS after WRITE command recognition.
0	0	This is a bit fixed to "0".

■ OP-CODE

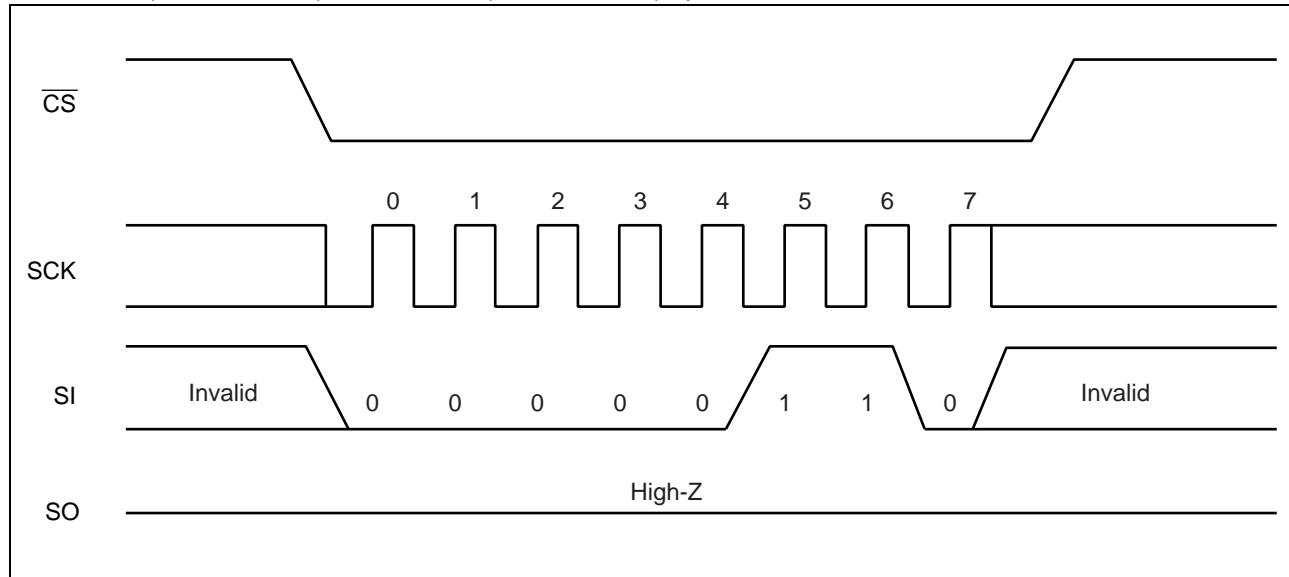
MB85RS512T accepts 9 kinds of command specified in op-code. Op-code is a code composed of 8 bits shown in the table below. Do not input invalid codes other than those codes. If CS is risen while inputting op-code, the command are not performed.

Name	Description	Op-code
WREN	Set Write Enable Latch	0000 0110 _B
WRDI	Reset Write Enable Latch	0000 0100 _B
RDSR	Read Status Register	0000 0101 _B
WRSR	Write Status Register	0000 0001 _B
READ	Read Memory Code	0000 0011 _B
WRITE	Write Memory Code	0000 0010 _B
RDID	Read Device ID	1001 1111 _B
FSTRD	Fast Read Memory Code	0000 1011 _B
SLEEP	Sleep Mode	1011 1001 _B

■ COMMAND

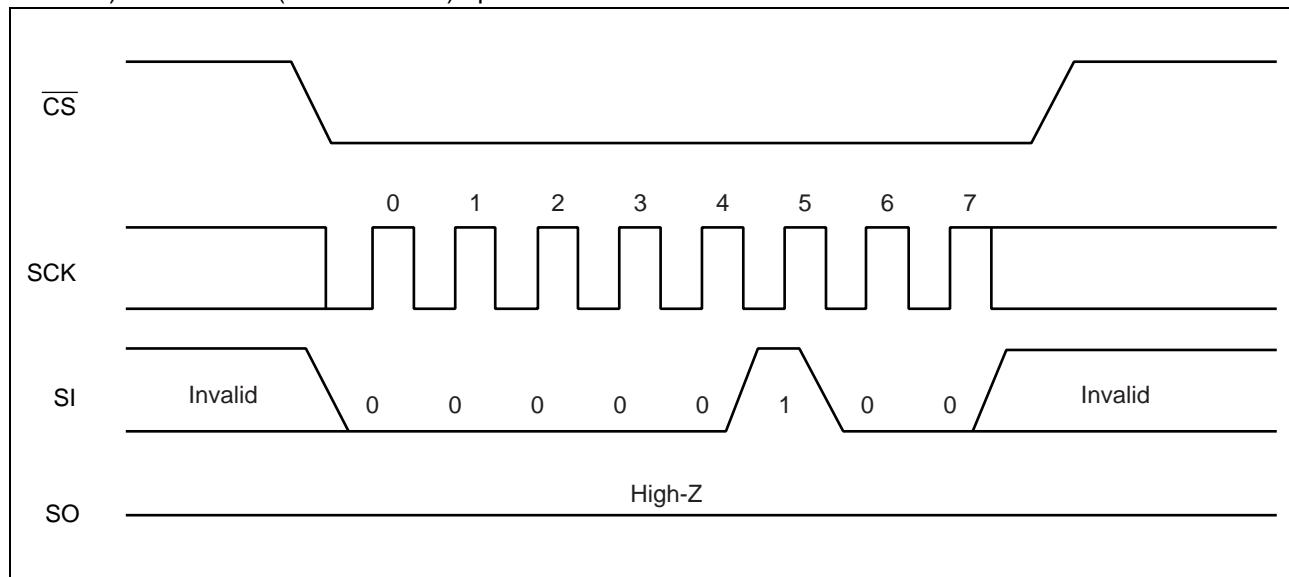
• WREN

The WREN command sets WEL (Write Enable Latch) . WEL has to be set with the WREN command before writing operation (WRSR command and WRITE command) . WREN command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



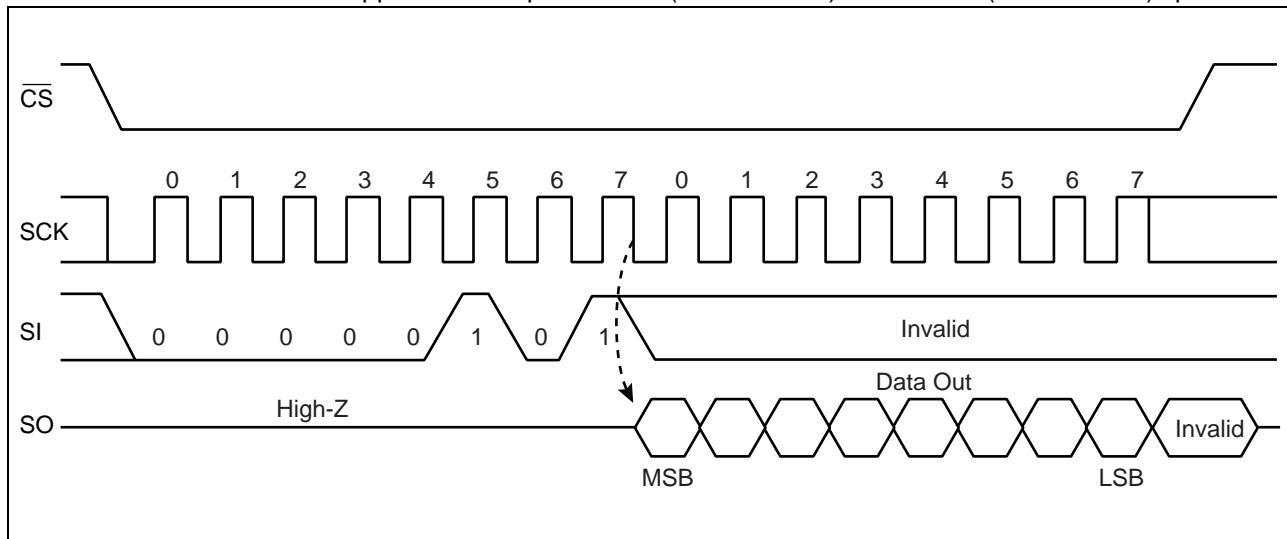
• WRDI

The WRDI command resets WEL (Write Enable Latch) . Writing operation (WRSR command and WRITE command) are not performed when WEL is reset. WRDI command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



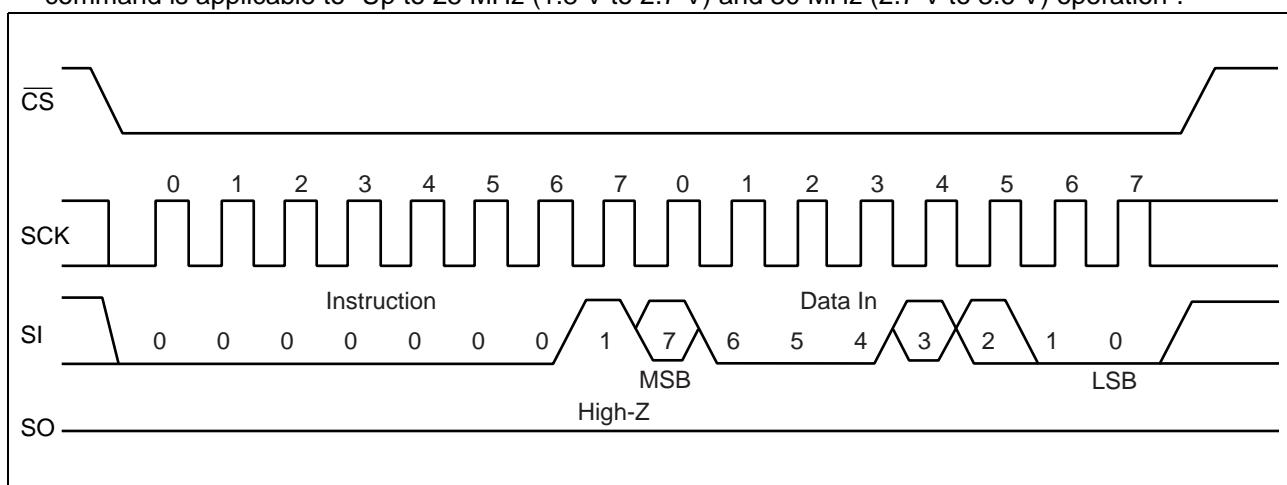
- **RDSR**

The RDSR command reads status register data. After op-code of RDSR is input to SI, 8-cycle clock is input to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK. In the RDSR command, repeated reading of status register is enabled by sending SCK continuously before rising of \overline{CS} . RDSR command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



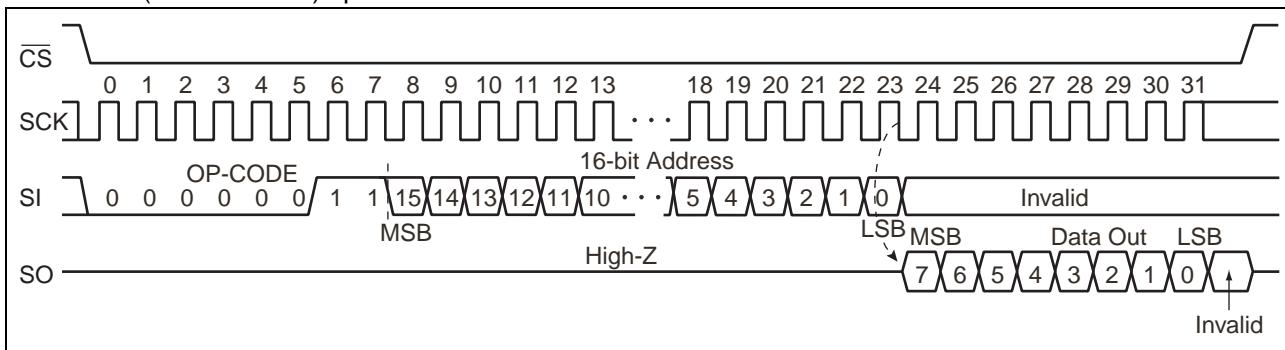
- **WRSR**

The WRSR command writes data to the nonvolatile memory bit of status register. After performing WRSR op-code to a SI pin, 8 bits writing data is input. WEL (Write Enable Latch) is not able to be written with WRSR command. A SI value correspondent to bit 1 is ignored. Bit 0 of the status register is fixed to “0” and cannot be written. The SI value corresponding to bit 0 is ignored. \overline{WP} signal level shall be fixed before performing WRSR command, and do not change the \overline{WP} signal level until the end of command sequence. WRSR command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



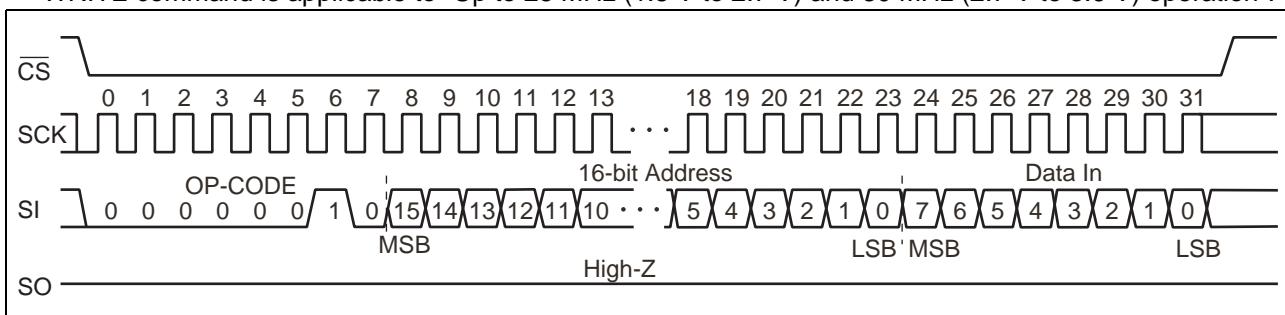
• READ

The READ command reads FRAM memory cell array data. Arbitrary 16 bits address and op-code of READ are input to SI. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When CS is risen, the READ command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before CS rising. When it reaches the most significant address, it rolls over to the starting address, and reading cycle keeps on infinitely. READ command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



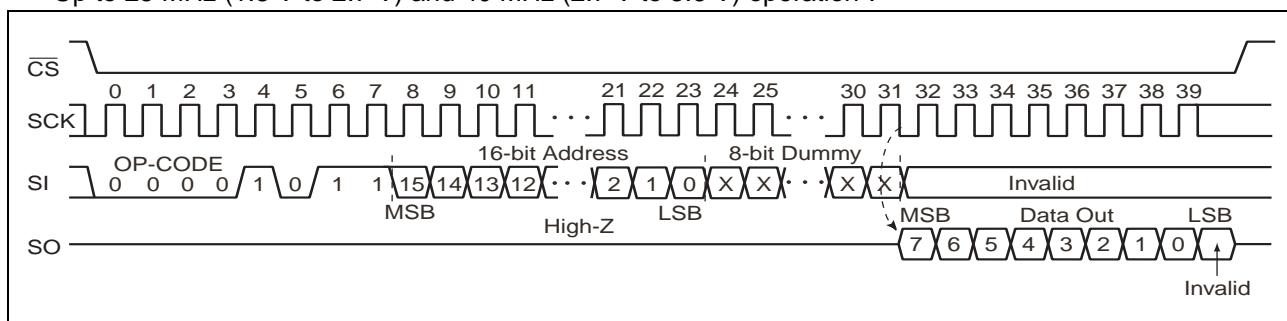
• WRITE

The WRITE command writes data to FRAM memory cell array. WRITE op-code, arbitrary 16 bits of address and 8 bits of writing data are input to SI. When 8 bits of writing data is input, data is written to FRAM memory cell array. Risen CS will terminate the WRITE command, but if you continue sending the writing data for 8 bits each before CS rising, it is possible to continue writing with automatic address increment. When it reaches the most significant address, it rolls over to the starting address, and writing cycle can be continued infinitely. WRITE command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



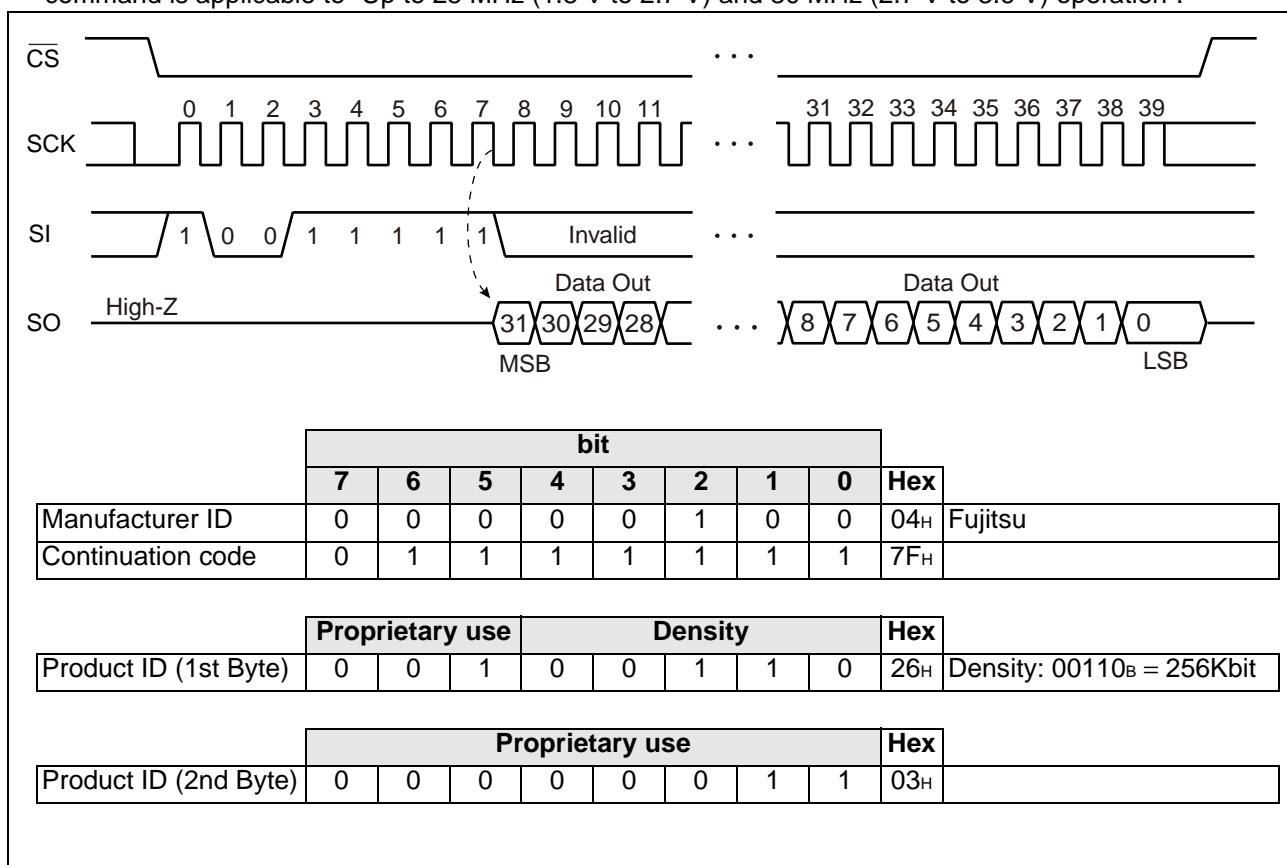
• FSTRD

The FSTRD command reads FRAM memory cell array data. Arbitrary 16 bits address and op-code of FSTRD are input to SI followed by 8 bits dummy. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When CS is risen, the FSTRD command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before CS rising. When it reaches the most significant address, it rolls over to the starting address, and reading cycle keeps on infinitely. FSTRD command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 40 MHz (2.7 V to 3.6 V) operation”.



• RDID

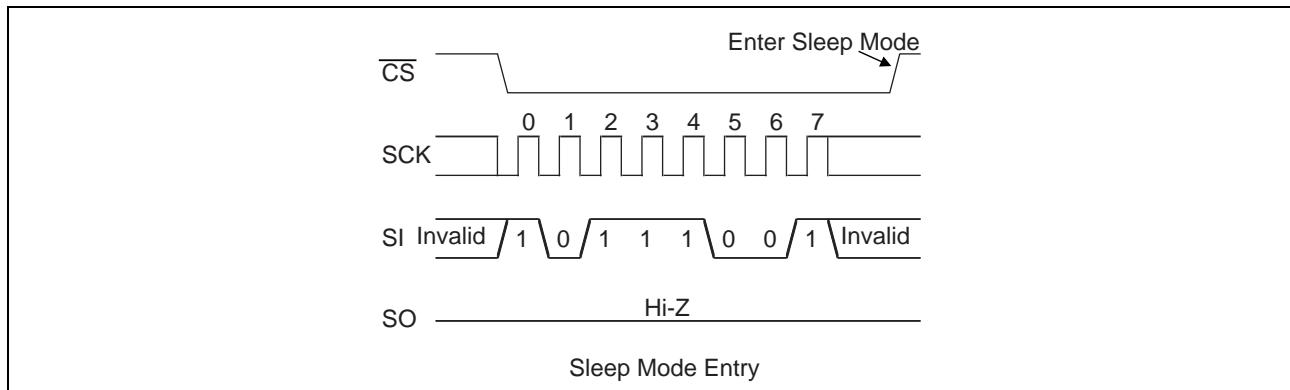
The RDID command reads fixed Device ID. After performing RDID op-code to SI, 32-cycle clock is input to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK. The output is in order of Manufacturer ID (8bit)/Continuation code (8bit)/Product ID (1st Byte)/Product ID (2nd Byte). In the RDID command, SO holds the output state of the last bit in 32-bit Device ID until CS is risen. RDID command is applicable to “Up to 25 MHz (1.8 V to 2.7 V) and 30 MHz (2.7 V to 3.6 V) operation”.



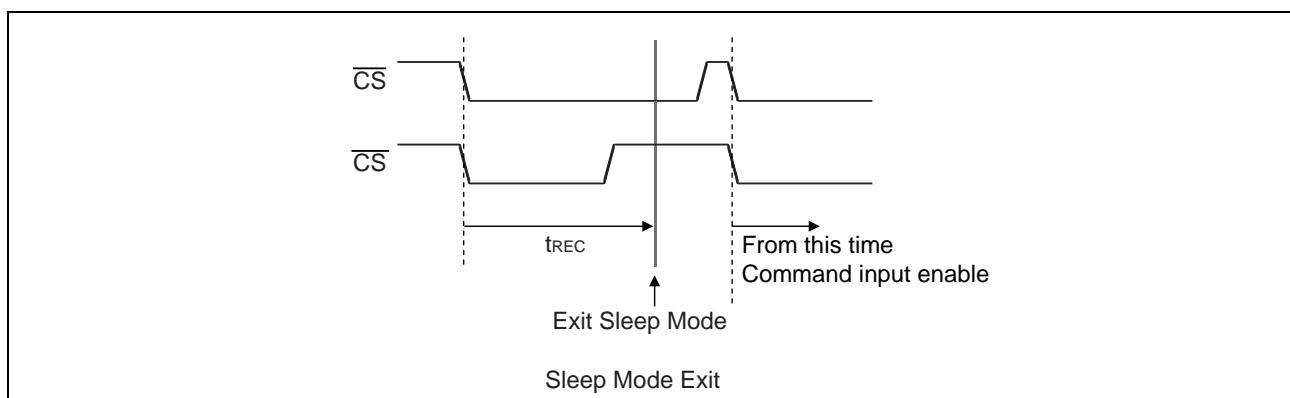
• SLEEP

The SLEEP command shifts the LSI to a low power mode called "SLEEP mode". The transition to the SLEEP mode is carried out at the rising edge of \overline{CS} after operation code in the SLEEP command. However, when at least one SCK clock is inputted before the rising edge of \overline{CS} after operation code in the SLEEP command, this SLEEP command is canceled.

After the SLEEP mode transition, SCK and SI inputs are ignored and SO changes to a Hi-Z state.



Returning to an normal operation from the SLEEP mode is carried out after t_{REC} (Max 400 μ s) time from the falling edge of \overline{CS} (see the figure below). It is possible to return \overline{CS} to H level before t_{REC} time. However, it is prohibited to bring down \overline{CS} to L level again during t_{REC} period.



■ BLOCK PROTECT

Writing protect block for WRITE command is configured by the value of BP0 and BP1 in the status register.

BP1	BP0	Protected Block
0	0	None
0	1	C000 _H to FFFF _H (upper 1/4)
1	0	8000 _H to FFFF _H (upper 1/2)
1	1	0000 _H to FFFF _H (all)

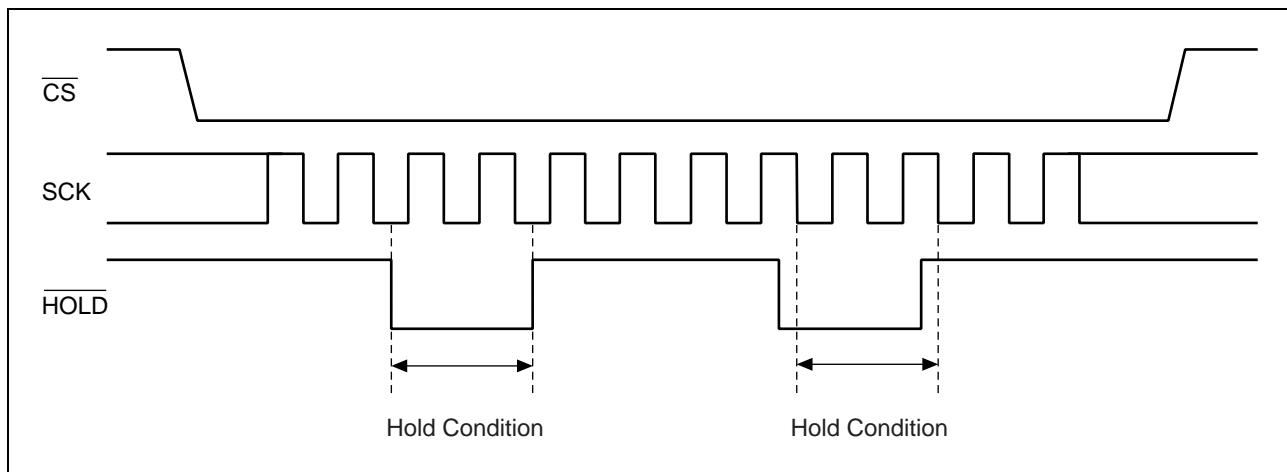
■ WRITING PROTECT

Writing operation of the WRITE command and the WRSR command are protected with the value of WEL, WPEN, WP as shown in the table.

WEL	WPEN	<u>WP</u>	Protected Blocks	Unprotected Blocks	Status Register
0	X	X	Protected	Protected	Protected
1	0	X	Protected	Unprotected	Unprotected
1	1	0	Protected	Unprotected	Protected
1	1	1	Protected	Unprotected	Unprotected

■ HOLD OPERATION

Hold status is retained without aborting a command if HOLD is “L” level while CS is “L” level. The timing for starting and ending hold status depends on the SCK to be “H” level or “L” level when a HOLD pin input is transited to the hold condition as shown in the diagram below. In case the HOLD pin transited to “L” level when SCK is “L” level, return the HOLD pin to “H” level at SCK being “L” level. In the same manner, in case the HOLD pin transited to “L” level when SCK is “H” level, return the HOLD pin to “H” level at SCK being “H” level. Arbitrary command operation is interrupted in hold status, SCK and SI inputs become do not care. And, SO becomes High-Z while reading command (RDSR, READ). If CS is rising during hold status, a command is aborted. In case the command is aborted before its recognition, WEL holds the value before transition to hold status.



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Unit
		Min	Max	
Power supply voltage*	V _{DD}	– 0.5	+ 4.0	V
Input voltage*	V _{IN}	– 0.5	V _{DD} + 0.5	V
Output voltage*	V _{OUT}	– 0.5	V _{DD} + 0.5	V
Operation ambient temperature	T _A	– 40	+ 85	°C
Storage temperature	T _{STG}	– 55	+ 125	°C

*: These parameters are based on the condition that V_{SS} is 0 V.

WARNING: Semiconductor devices may be permanently damaged by application of stress (including, without limitation, voltage, current or temperature) in excess of absolute maximum ratings.
Do not exceed any of these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Power supply voltage*	V _{DD}	1.8	3.3	3.6	V
Input high voltage*	V _{IH}	V _{DD} × 0.7	—	V _{DD} + 0.5	V
Input low voltage*	V _{IL}	– 0.5	—	V _{DD} × 0.3	V
Operation ambient temperature	T _A	– 40	—	+ 85	°C

*: These parameters are based on the condition that V_{SS} is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated under these conditions.

Any use of semiconductor devices will be under their recommended operating condition.
Operation under any conditions other than these conditions may adversely affect reliability of device and could result in device failure.

No warranty is made with respect to any use, operating conditions or combinations not represented on this data sheet. If you are considering application under any conditions other than listed herein, please contact sales representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol	Condition	Value			Unit
			Min	Typ	Max	
Input leakage current* ¹	I _{IL}	0 ≤ CS < V _{DD}	—	—	200	μA
		CS = V _{DD}	—	—	1	
		WP, HOLD, SCK SI = 0 V to V _{DD}	—	—	1	
Output leakage current* ²	I _{LO}	SO = 0 V to V _{DD}	—	—	1	μA
Operating power supply current	I _{DD}	SCK = 30 MHz	—	—	10	mA
Standby current	I _{SB}	SCK = SI = CS = V _{DD}	—	25	120	μA
Sleep current	I _{zz}	CS = V _{DD} All inputs V _{SS} or V _{DD}	—	—	10	μA
Output high voltage	V _{OH}	I _{OH} = -2 mA	V _{DD} - 0.5	—	—	V
Output low voltage	V _{OL}	I _{OL} = 2 mA	—	—	0.4	V
Pull up resistance for CS	R _P	—	18	33	80	kΩ

*1 : Applicable pin : CS, WP, HOLD, SCK, SI

*2 : Applicable pin : SO

2. AC Characteristics

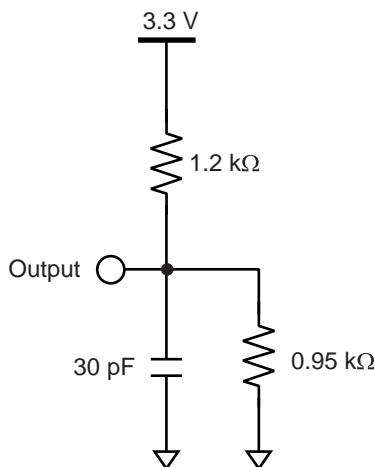
Parameter	Symbol	Value				Unit	
		Up to 25 MHz operation* ¹ (V _{DD} = 1.8 V to 2.7 V)		Up to 30 MHz operation* ² (V _{DD} = 2.7 V to 3.6 V)			
		Min	Max	Min	Max		
SCK clock frequency (All commands except FSTRD command)	f _{Ck}	0	25	0	30	MHz	
SCK clock frequency (for FSTRD command)	f _{Ck}	0	25	0	40	MHz	
Clock high time	t _{CH}	15	—	11	—	ns	
Clock low time	t _{CL}	15	—	11	—	ns	
Chip select set up time	t _{Csu}	10	—	10	—	ns	
Chip select hold time	t _{Csh}	10	—	10	—	ns	
Output disable time	t _{OD}	—	12	—	12	ns	
Output data valid time	t _{ODV}	—	18	—	9	ns	
Output hold time	t _{OH}	0	—	0	—	ns	
Deselect time	t _D	40	—	40	—	ns	
Data in rising time	t _R	—	50	—	50	ns	
Data falling time	t _F	—	50	—	50	ns	
Data set up time	t _{SU}	5	—	5	—	ns	
Data hold time	t _H	5	—	5	—	ns	
HOLD set uptime	t _{HS}	10	—	10	—	ns	
HOLD hold time	t _{HH}	10	—	10	—	ns	
HOLD output floating time	t _{HZ}	—	20	—	20	ns	
HOLD output active time	t _{LZ}	—	20	—	20	ns	
SLEEP recovery time	t _{REC}	—	400	—	400	μs	

*1 : All commands except FSTRD are applicable to "Up to 25 MHz operation" in V_{DD} = 1.8 V to 2.7 V.

*2 : All commands except FSTRD are applicable to "Up to 30 MHz operation" in V_{DD} = 2.7 V to 3.6 V.

AC Test Condition

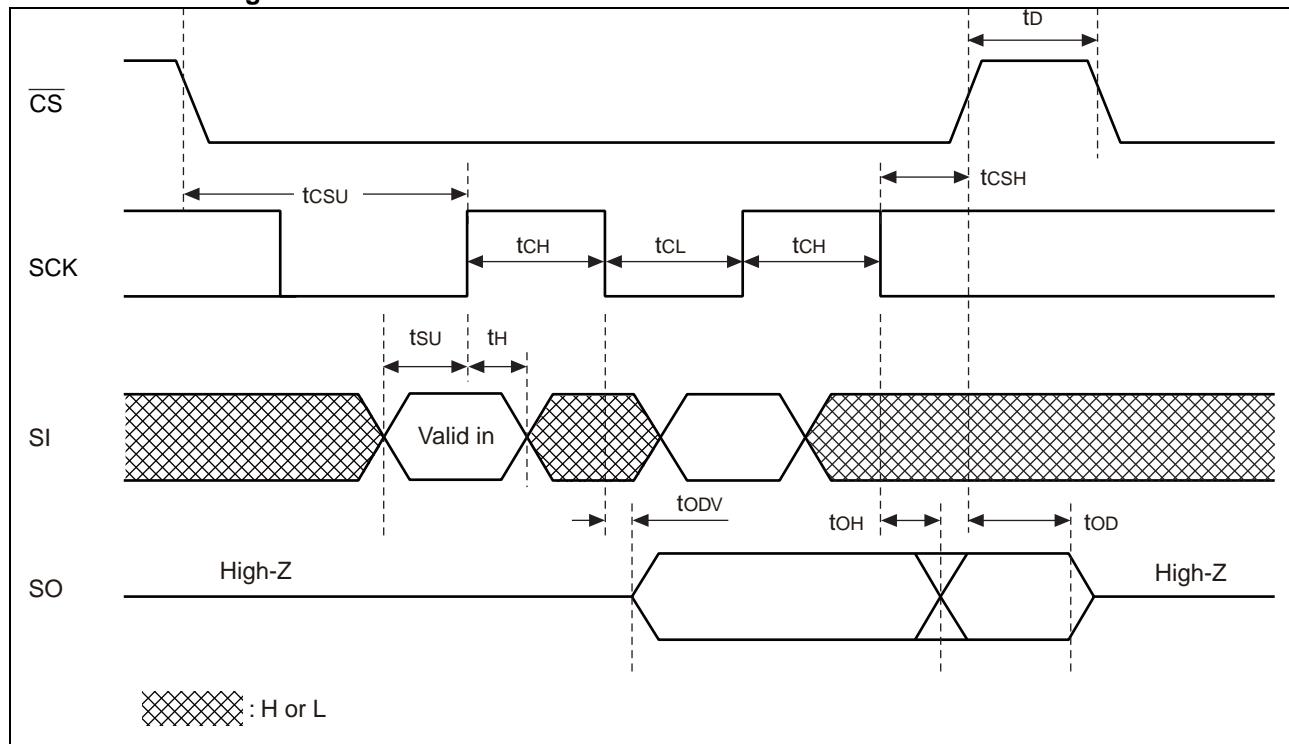
- Power supply voltage : 1.8 V to 3.6 V
- Operation ambient temperature : -40 °C to +85 °C
- Input voltage magnitude : V_{DD} × 0.8 ≤ V_{IH} ≤ V_{DD}
0 ≤ V_{IL} ≤ V_{DD} × 0.2
- Input rising time : 5 ns
- Input falling time : 5 ns
- Input judge level : V_{DD}/2
- Output judge level : V_{DD}/2

AC Load Equivalent Circuit**3. Pin Capacitance**

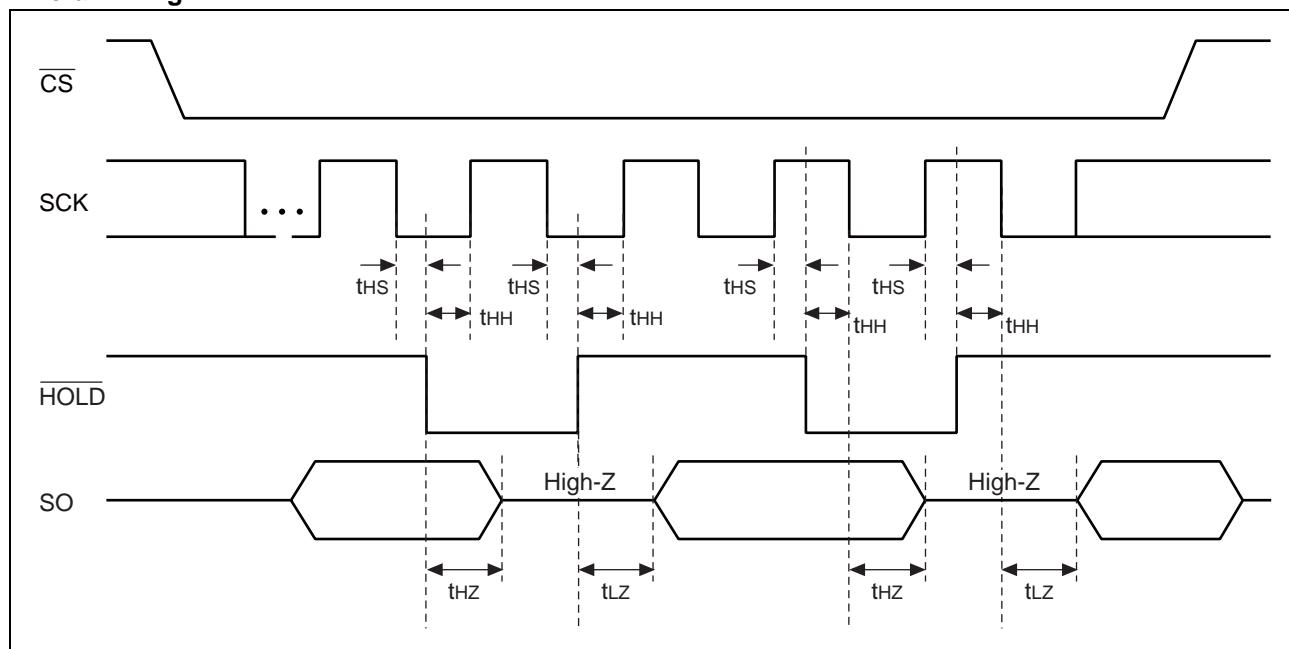
Parameter	Symbol	Condition	Value		Unit
			Min	Max	
Output capacitance	C_o	$V_{DD} = V_{IN} = V_{OUT} = 3.3 \text{ V}$, $f = 1 \text{ MHz}$, $T_A = +25^\circ\text{C}$	—	8	pF
Input capacitance	C_i		—	6	pF

■ TIMING DIAGRAM

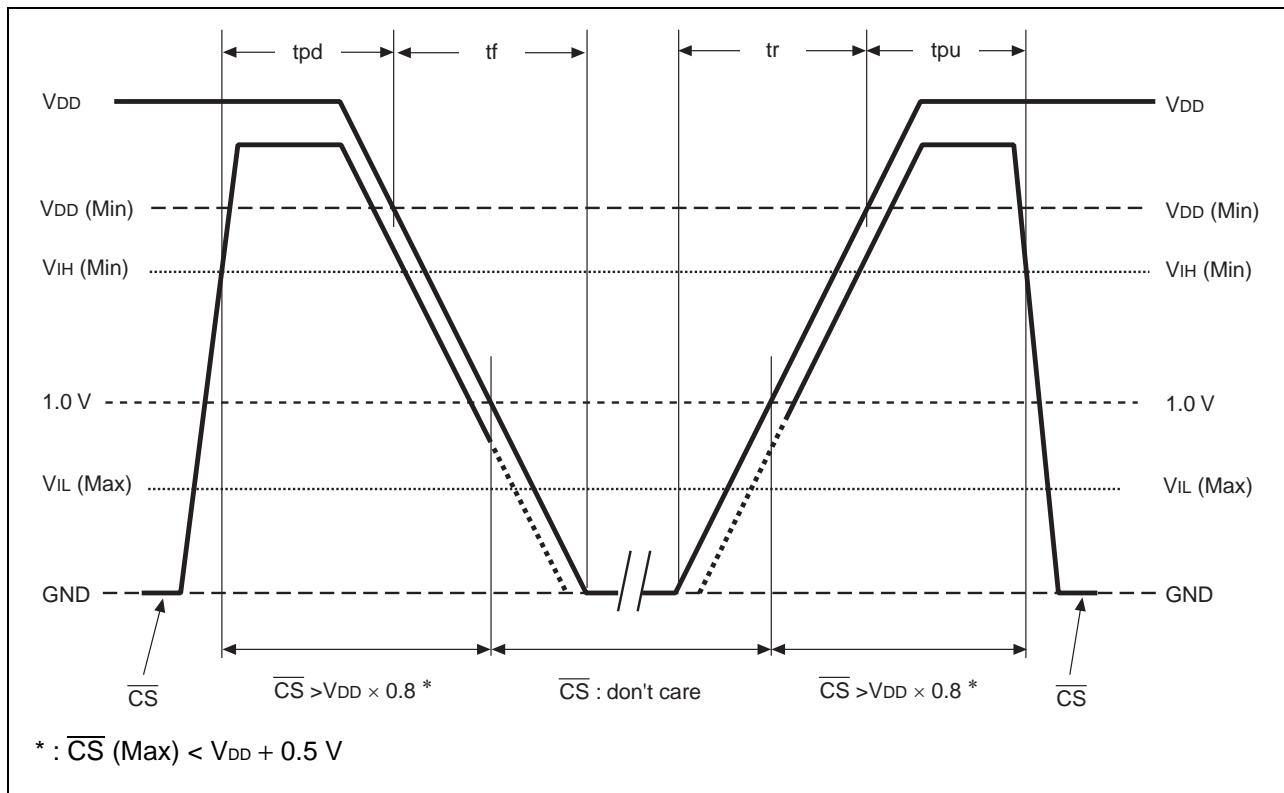
- Serial Data Timing



- Hold Timing



■ POWER ON/OFF SEQUENCE



Parameter	Symbol	Value		Unit
		Min	Max	
CS level hold time at power OFF	tpd	400	—	ns
CS level hold time at power ON	tpu	250	—	μs
Power supply rising time	tr	0.05	—	ms/V
Power supply falling time	tf	0.1	—	ms/V

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

■ FRAM CHARACTERISTICS

Parameter	Value		Unit	Remarks
	Min	Max		
Read/Write Endurance	10^{13}	—	Times/byte	Operation Ambient Temperature $T_A = +85^\circ\text{C}$ Total numbers of reading and writing
Data Retention	10	—	Years	Operation Ambient Temperature $T_A = +85^\circ\text{C}$ Retention time of the first reading/writing data right after shipment

Note : Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

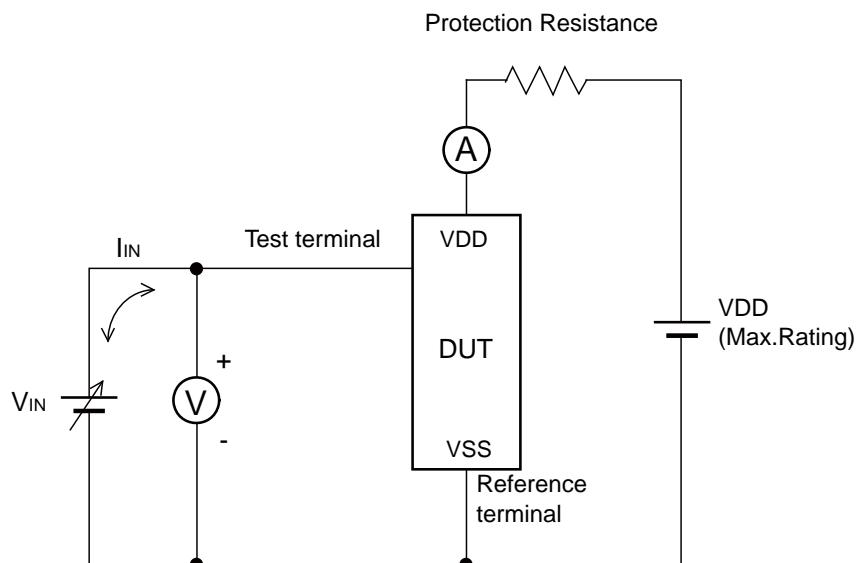
■ NOTE ON USE

We recommend programming of the device after reflow. Data written before reflow cannot be guaranteed.

■ ESD AND LATCH-UP

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant	MB85RS512TPNF-G-JNE1	$\geq 2000\text{ V} $
ESD MM (Machine Model) JESD22-A115 compliant		$\geq 200\text{ V} $
ESD CDM (Charged Device Model) JESD22-C101 compliant		—
Latch-Up (I-test) JESD78 compliant		—
Latch-Up (V_{supply} overvoltage test) JESD78 compliant		—
Latch-Up (Current Method) Proprietary method		—
Latch-Up (C-V Method) Proprietary method		—

- Current method of Latch-Up Resistance Test

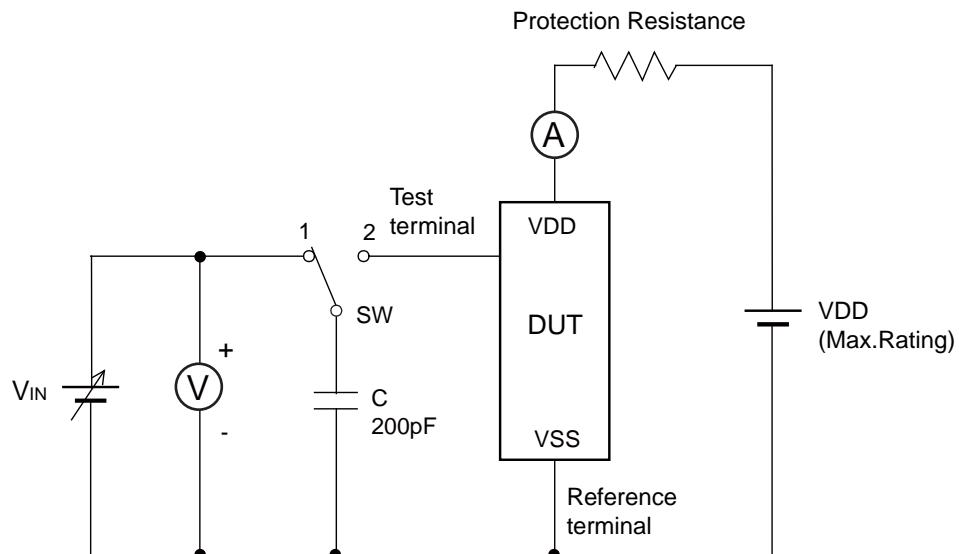


Note : The voltage V_{IN} is increased gradually and the current I_{IN} of 300 mA at maximum shall flow.

Confirm the latch up does not occur under $I_{\text{IN}} = \pm 300\text{ mA}$.

In case the specific requirement is specified for I/O and I_{IN} cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement.

- C-V method of Latch-Up Resistance Test



Note : Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle. Repeat this process 5 times. However, if the latch-up condition occurs before completing 5times, this test must be stopped immediately.

■ REFLOW CONDITIONS AND FLOOR LIFE

[JEDEC MSL] : Moisture Sensitivity Level 3 (ISP/JEDEC J-STD-020D)

■ Current status on Contained Restricted Substances

This product complies with the regulations of REACH Regulations, EU RoHS Directive and China RoHS. Please refer to the following web site for more details of current status on contained restricted substances in our products.

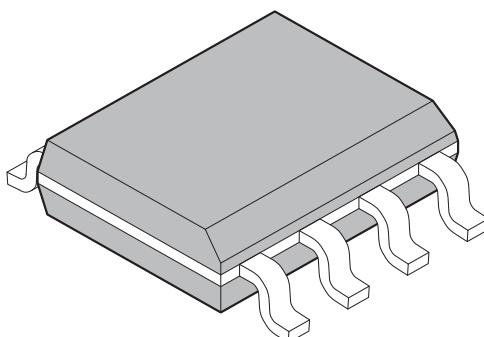
<http://www.fujitsu.com/global/services/microelectronics/environment/products/>

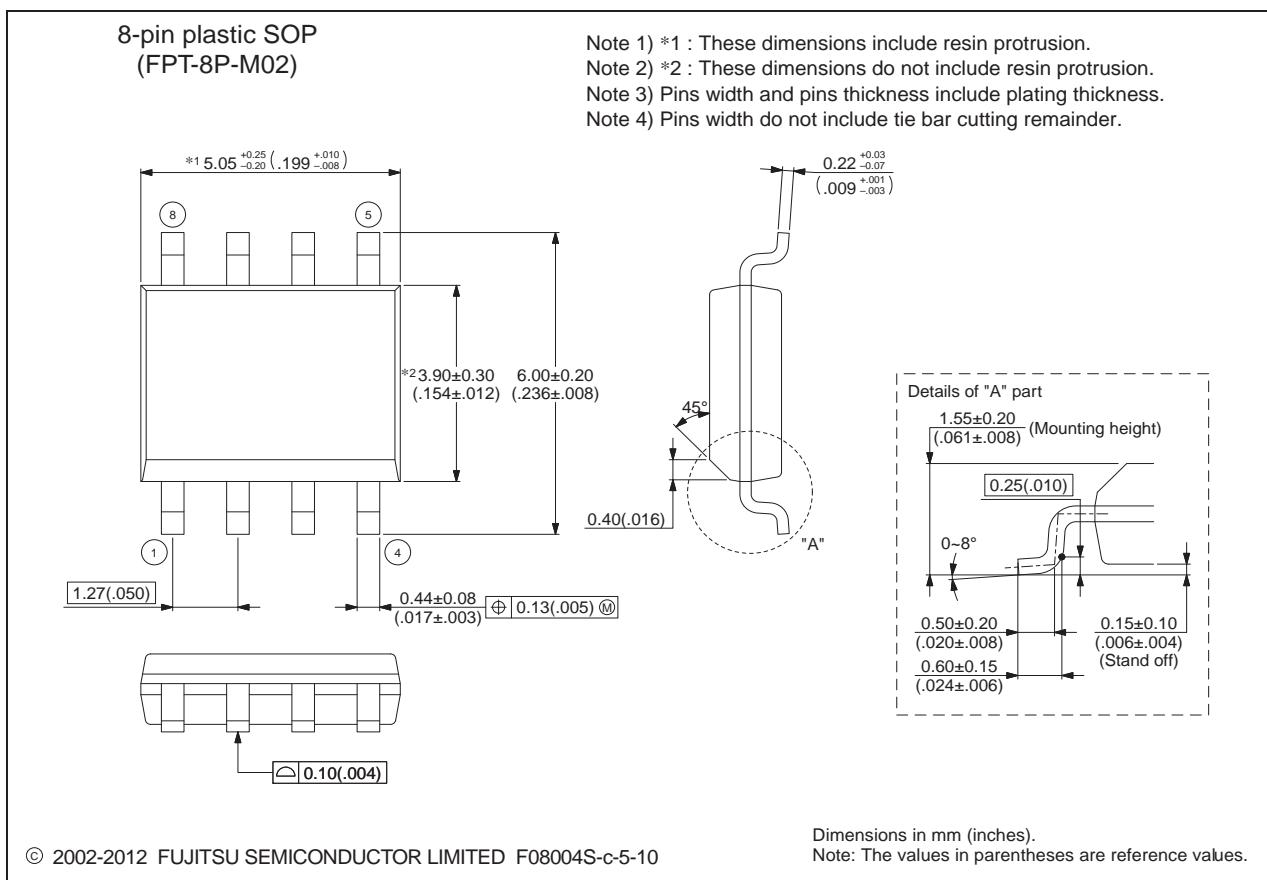
■ ORDERING INFORMATION

Part number	Package	Shipping form	Minimum shipping quantity
MB85RS512TPNF-G-JNE1	8-pin plastic SOP (FPT-8P-M02)	Tube	—*
MB85RS512TPNF-G-JNERE1	8-pin plastic SOP (FPT-8P-M02)	Embossed Carrier tape	1500

* : Please contact our sales office about minimum shipping quantity.

■ PACKAGE DIMENSION

 <p>8-pin plastic SOP (FPT-8P-M02)</p>	Lead pitch 1.27 mm
	Package width × package length 3.9 mm × 5.05 mm
	Lead shape Gullwing
	Sealing method Plastic mold
	Mounting height 1.75 mm MAX
	Weight 0.06 g



Please check the latest package dimension at the following URL.
<http://edevice.fujitsu.com/package/en-search/>

■ MARKING

[MB85RS512TPNF-G-JNE1]
[MB85RS512TPNF-G-JNERE1]



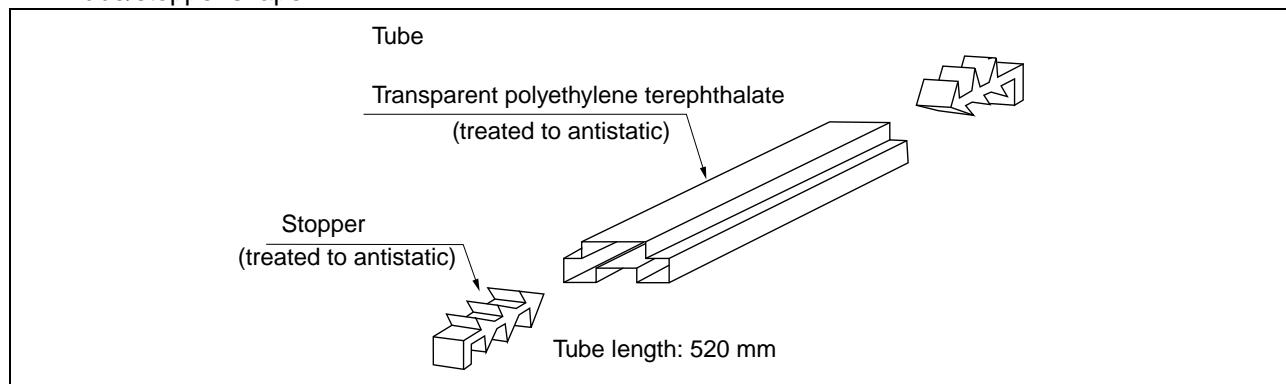
[FPT-8P-M02]

■ PACKING INFORMATION

1. Tube

1.1 Tube Dimensions

- Tube/stopper shape



Tube cross-sections and Maximum quantity

Package form	Package code	Maximum quantity		
		pcs/tube	pcs/inner box	pcs/outer box
SOP, 8, plastic (2)	FPT-8P-M02	95	7600	30400

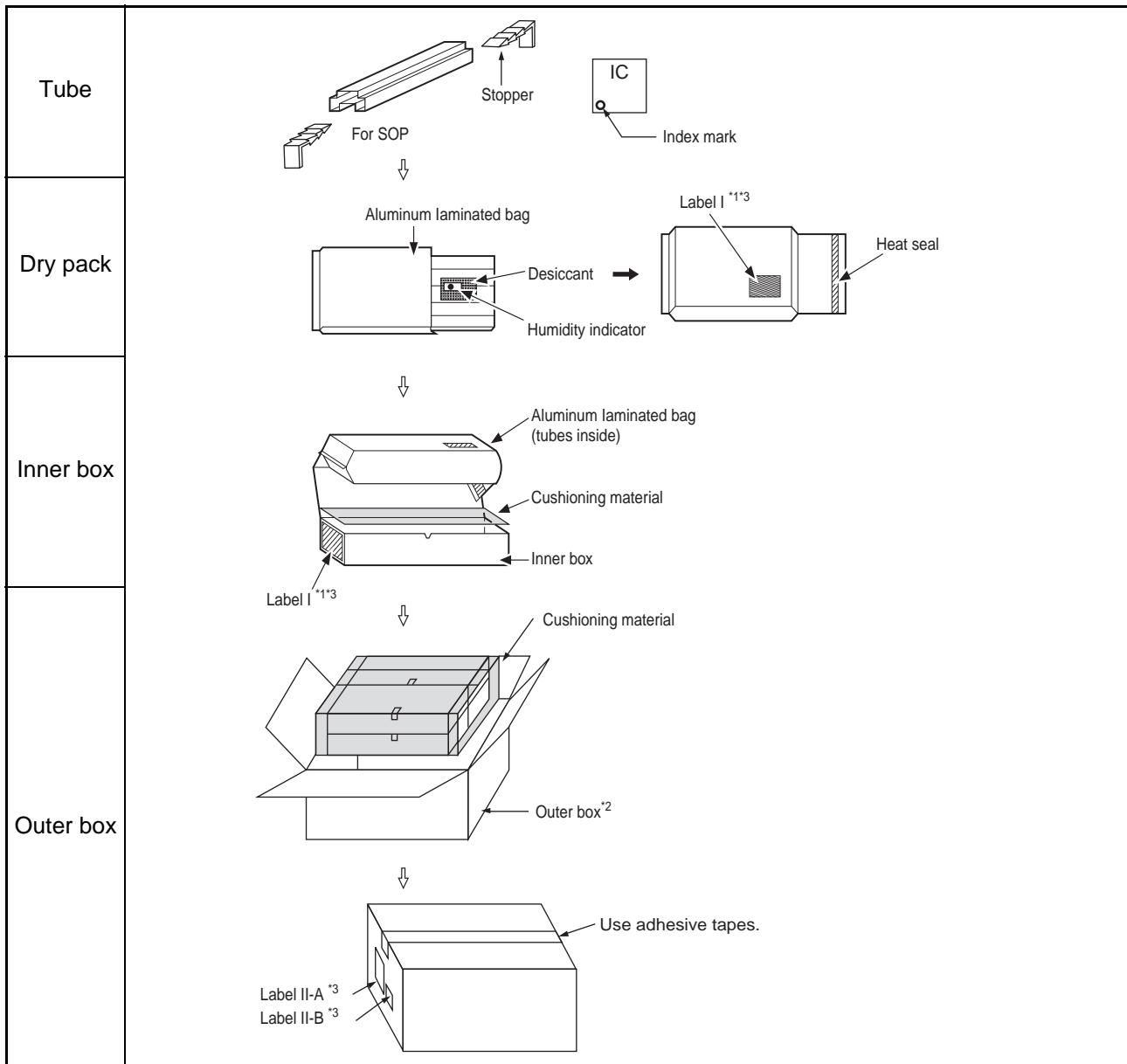
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F08008-SET1-PET:FJ99L-0022-E0008-1-K-3

$t = 0.5$
Transparent polyethylene terephthalate

The cross-sectional diagram shows a rectangular package with internal features. The total width is indicated as 7.4, the inner width as 6.4, the height as 1.8, and the thickness as $t = 0.5$. The diagram includes a scale bar at the bottom.

(Dimensions in mm)

1.2 Tube Dry pack packing specifications



*1: For a product of which part number is suffixed with "E1", a " " marks is displayed to the moisture barrier bag and the inner boxes.

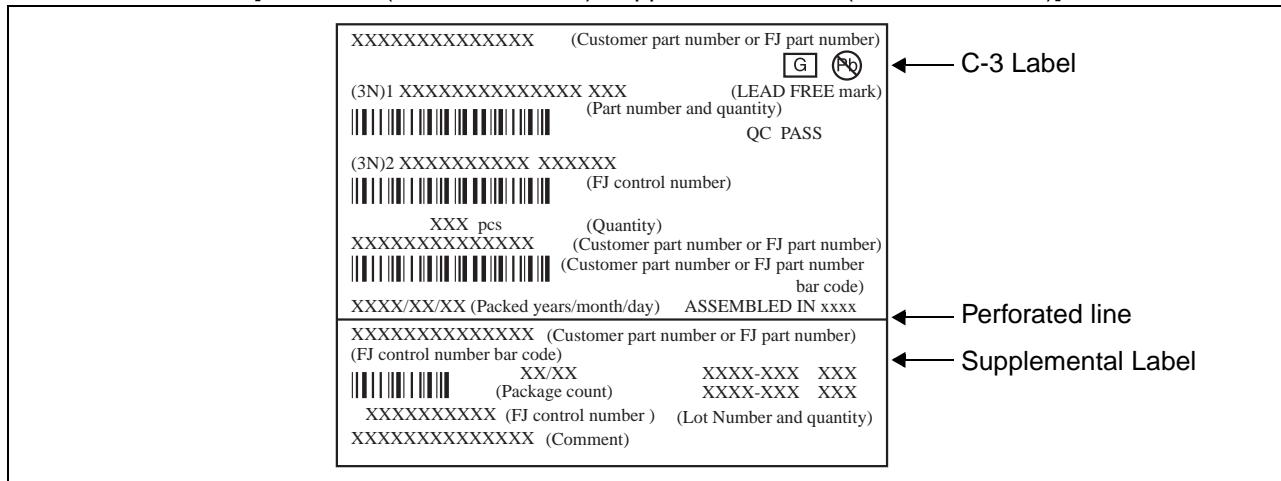
*2: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

*3: Please refer to an attached sheet about the indication label.

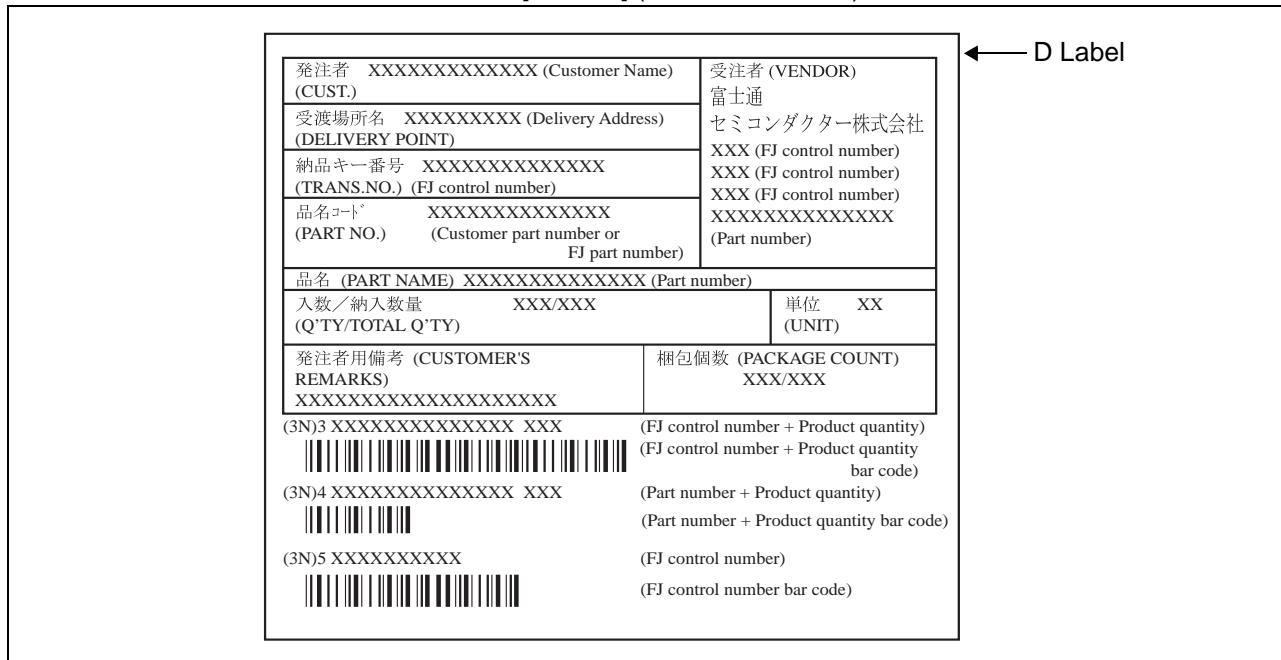
Note: The packing specifications may not be applied when the product is delivered via a distributor.

1.3 Product label indicators

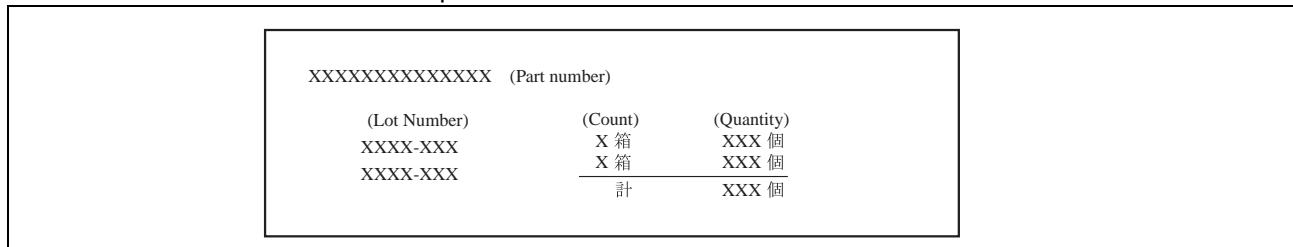
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping)
[C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



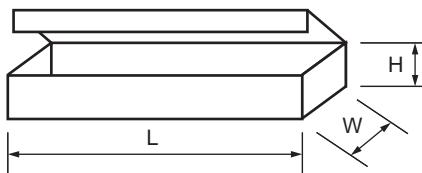
Label II-A: Label on Outer box [D Label] (100mm × 100mm)



Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

1.4 Dimensions for Containers**(1) Dimensions for inner box**

L	W	H
540	125	75

(Dimensions in mm)

(2) Dimensions for outer box

L	W	H
565	270	180

(Dimensions in mm)

2. Emboss Tape

2.1 Tape Dimensions

PKG code	Reel No	Maximum storage capacity		
		pcs/reel	pcs/inner box	pcs/outer box
FPT-8P-M02	3	1500	1500	10500

Technical drawing showing the front view of the emboss tape. The reel has a diameter of 1.75 ± 0.1 mm. There are 1500 pieces per reel, arranged in 15 rows of 10 pieces each. The distance between rows is 5.5 ± 0.05 mm. The width of the reel is 12 ± 0.1 mm. The distance between the centers of adjacent pieces in a row is 4 ± 0.1 mm. The distance between the centers of adjacent rows is 2 ± 0.05 mm. The outer diameter of the reel is 1.5 ± 0.1 mm. A cross-sectional view labeled SEC.B-B shows the thickness of the tape as 0.3 ± 0.05 mm.

Technical drawing showing a cross-sectional view of the emboss tape. The total height of the tape is 5.5 ± 0.1 mm. The thickness of the tape is 0.4 ± 0.1 mm. The distance from the bottom of the tape to the top of the substrate is 2.1 ± 0.1 mm. The distance from the center of the tape to the edge of the substrate is 3.9 ± 0.2 mm. The total width of the tape is 6.4 ± 0.1 mm.

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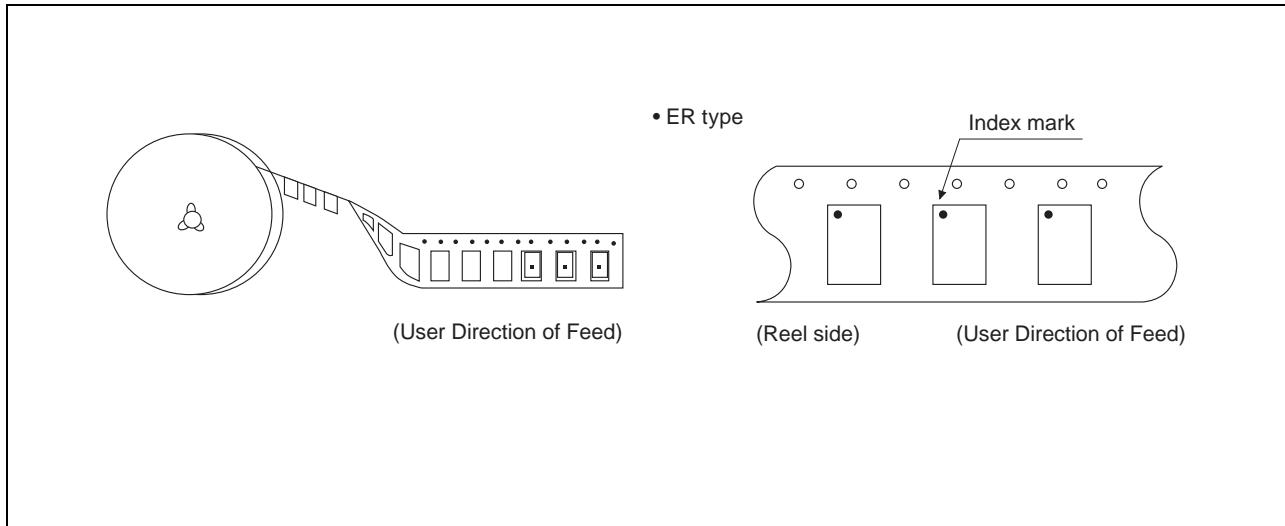
(Dimensions in mm)

Material : Conductive polystyrene

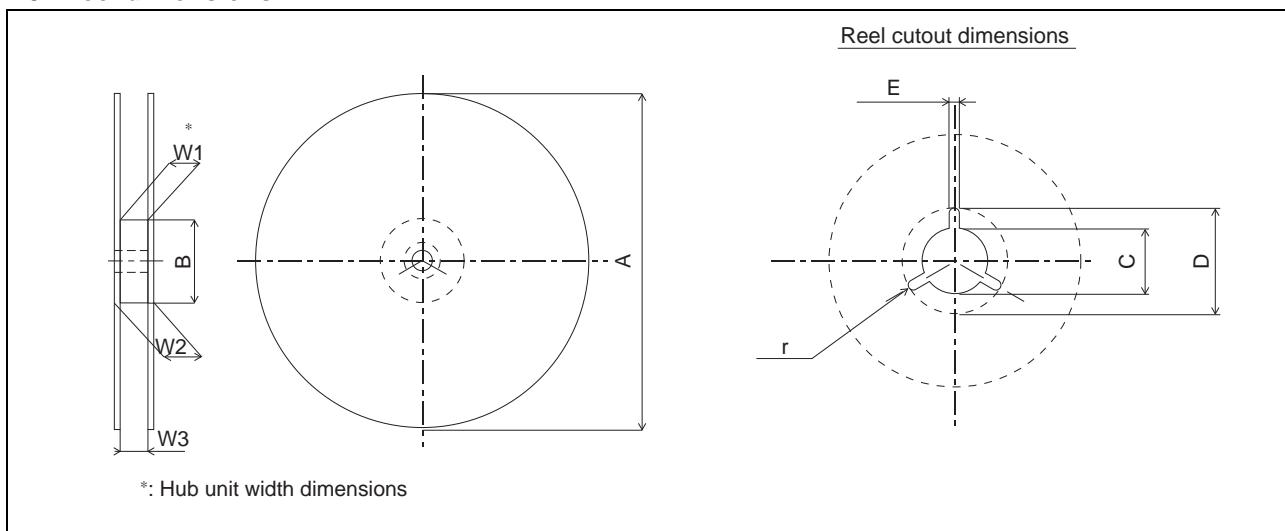
Heat proof temperature : No heat resistance.

Package should not be baked
by using tape and reel.

2.2 IC orientation

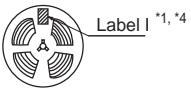
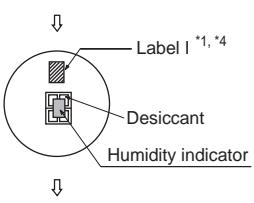
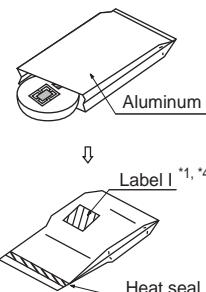


2.3 Reel dimensions



Dimensions in mm															
Reel No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
Tape width Symbol	8	12		16		24		32		44		56	12	16	24
A	254 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2								330 ± 2
B				100 . ² ₀				100 . ² ₀	150 . ² ₀	100 . ² ₀	150 . ² ₀	100 . ² ₀		100 ± 2	
C					13 ± 0.2										13 . ^{0.5} ₂
D						21 ± 0.8									20.5 . ¹ ₂
E							2 ± 0.5								
W1	8.4 . ² ₀	12.4 . ² ₀	16.4 . ² ₀	24.4 . ² ₀	32.4 . ² ₀	44.4 . ² ₀	56.4 . ² ₀	12.4 . ¹ ₀	16.4 . ¹ ₀	24.4 . ^{0.1} ₀					
W2	less than 14.4	less than 18.4	less than 22.4	less than 30.4	less than 38.4	less than 50.4	less than 62.4	less than 18.4	less than 22.4	less than 30.4					
W3	7.9 ~ 10.9	11.9 ~ 15.4	15.9 ~ 19.4	23.9 ~ 27.4	31.9 ~ 35.4	43.9 ~ 47.4	55.9 ~ 59.4	12.4 ~ 14.4	16.4 ~ 18.4	24.4 ~ 26.4					
r					1.0										

2.4 Taping (φ330mm Reel) Dry Pack Packing Specifications

	Outside diameter: φ 330mm reel
Embossed tapes	
Dry pack	
Inner box	
Outer box	
	<p>Use adhesive tapes.</p> <p>Label II-A *4</p> <p>Label II-B *4</p>

*1: For a product of which part number is suffixed with "E1", a "G"  marks is displayed to the moisture barrier bag and the inner boxes.

*2: The size of the outer box may be changed depending on the quantity of inner boxes.

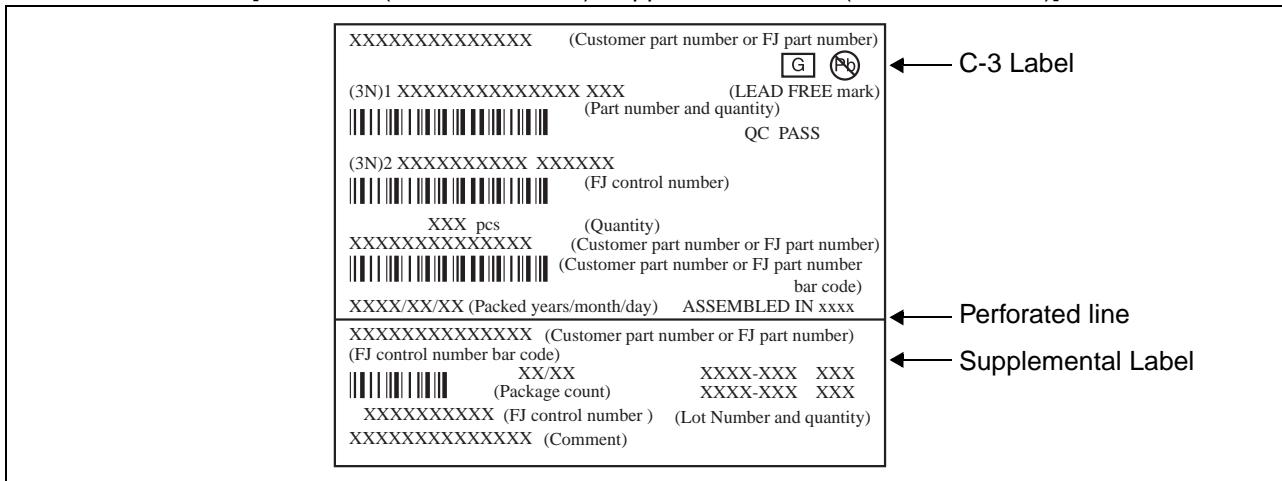
*3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

*4: Please refer to an attached sheet about the indication label.

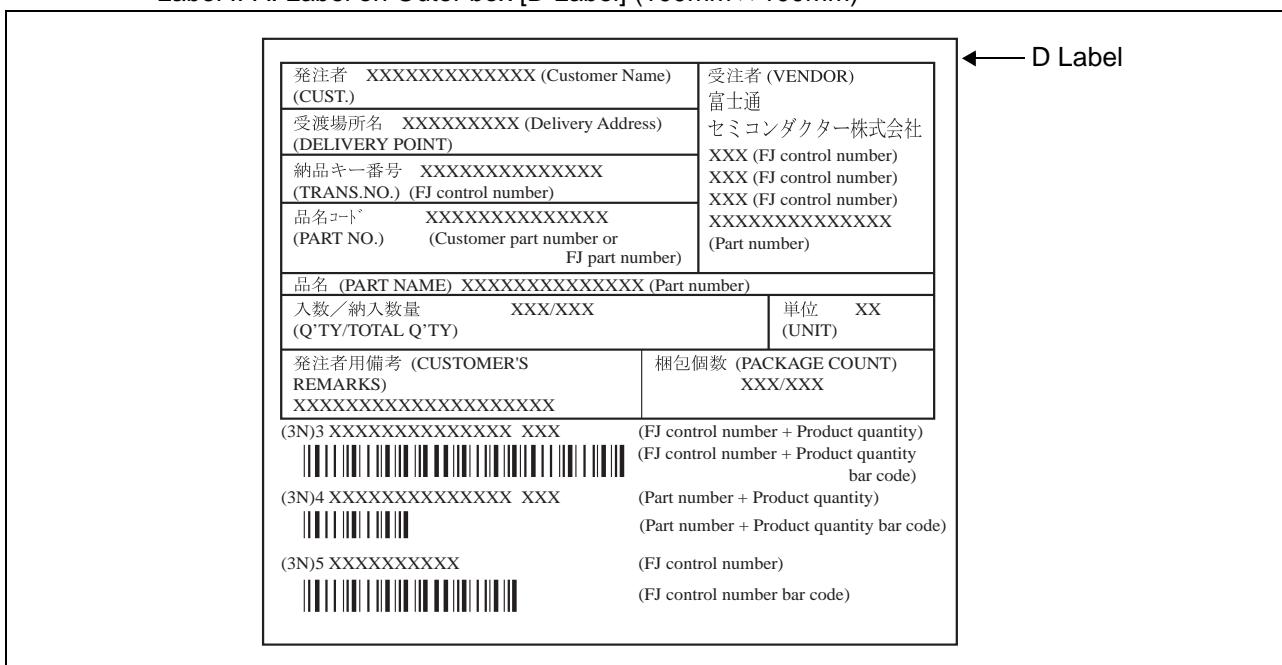
Note: The packing specifications may not be applied when the product is delivered via a distributor.

2.5 Product label indicators

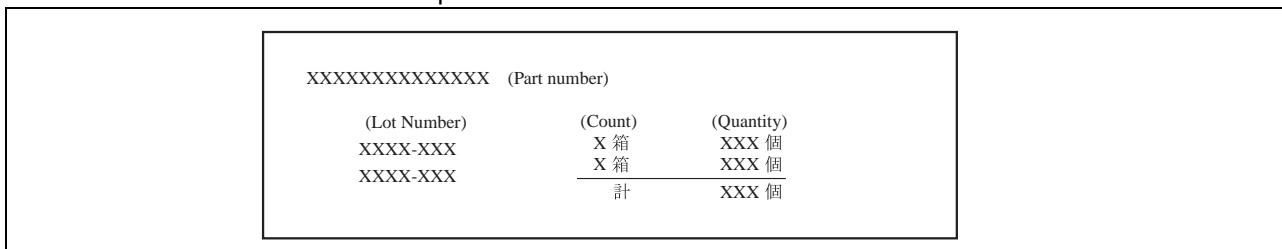
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping)
[C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



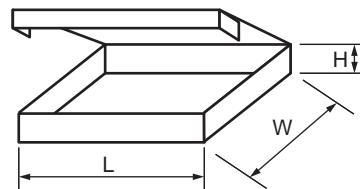
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

2.6 Dimensions for Containers

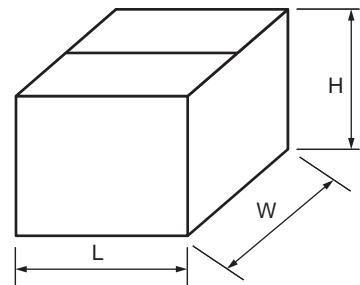
(1) Dimensions for inner box



Tape width	L	W	H
12, 16	365	345	40
24, 32			50
44			65
56			75

(Dimensions in mm)

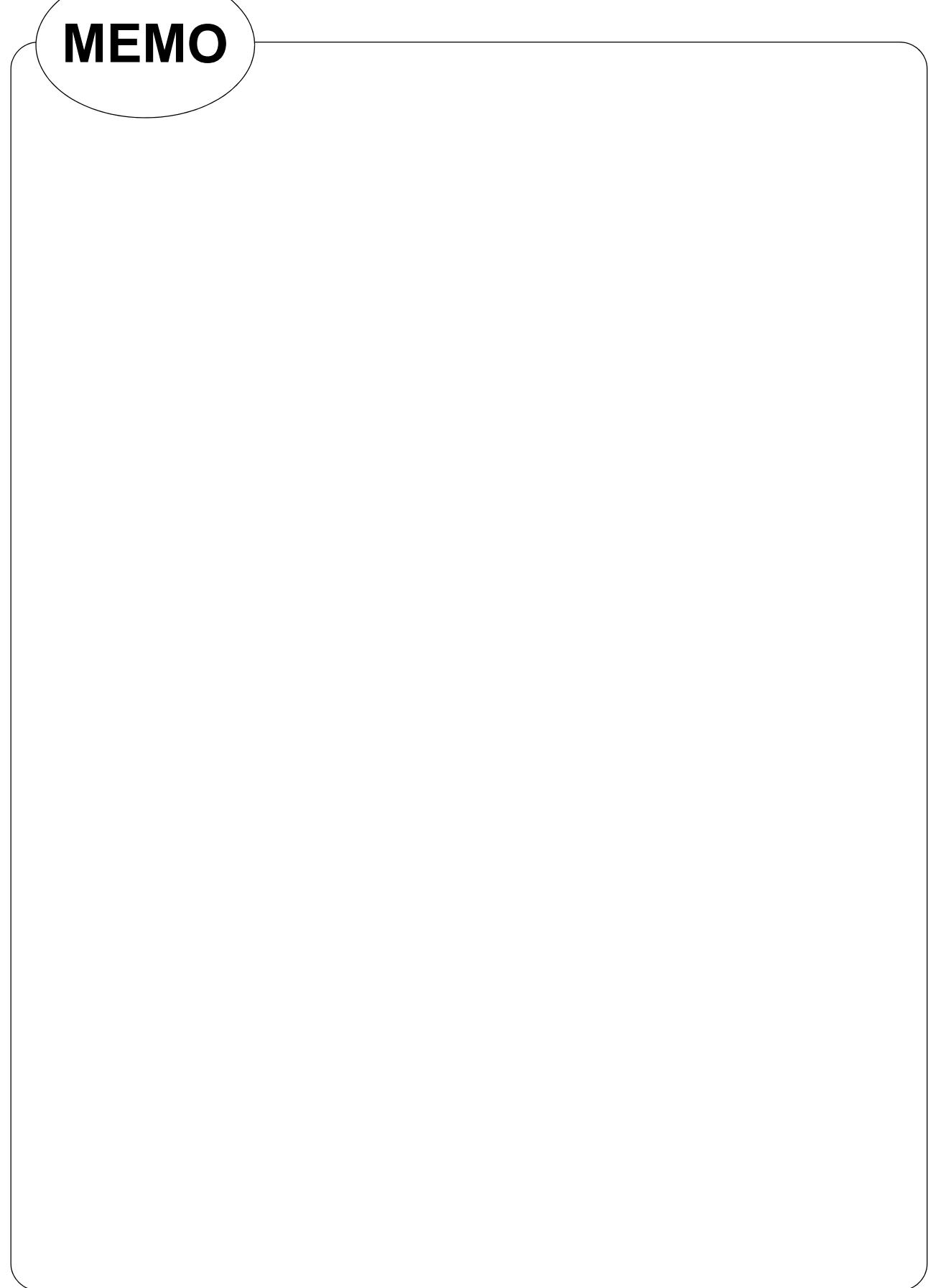
(2) Dimensions for outer box



L	W	H
415	400	315

(Dimensions in mm)

MEMO



MEMO

MEMO

FUJITSU SEMICONDUCTOR LIMITED

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